

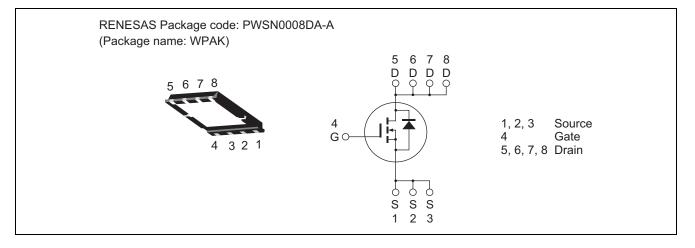
Silicon N Channel Power MOS FET Power Switching

REJ03G1251-0200 Rev.2.00 Aug 28, 2009

Features

- Low on-resistance
- Low drive current
- High density mounting

Outline



Absolute Maximum Ratings

			$(Ta = 25^{\circ}C)$
Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	200	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	8.5	А
Drain peak current	I _{D (pulse)} Note1	17	А
Body-drain diode reverse drain current	I _{DR}	8.5	А
Body-drain diode reverse drain peak current	Note1 I _{DR (pulse)}	17	А
Avalanche current	I _{AP} ^{Note3}	8.5	А
Avalanche energy	E _{AR} ^{Note3}	4.8	mJ
Channel dissipation	Pch Note2	20	W
Channel to case thermal impedance	θch-c	6.25	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tc = 25°C

3. STch = 25°C, Tch \leq 150°C



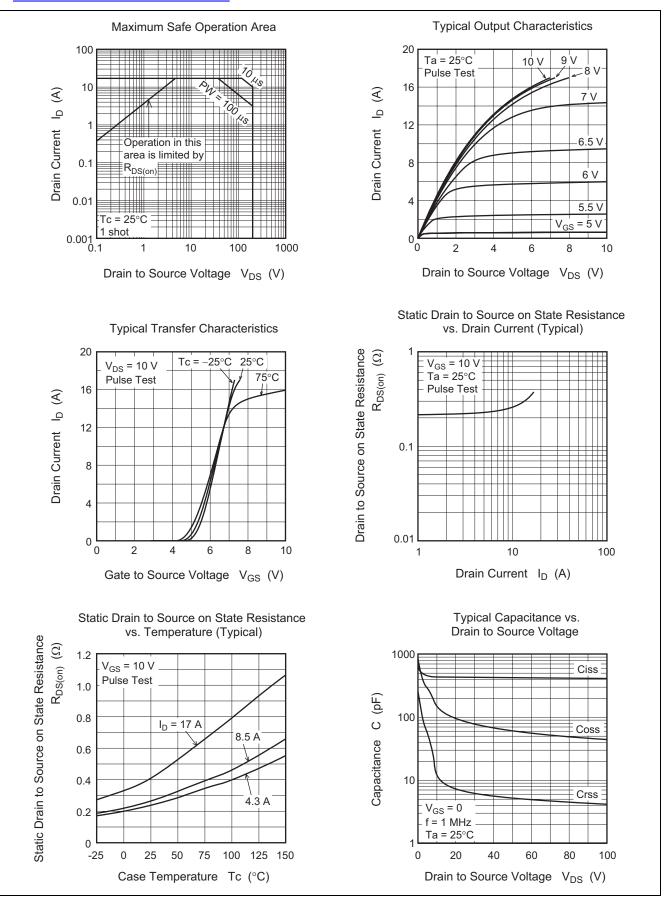
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	-					$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	200	—		V	I _D = 10 mA, V _{GS} = 0
Zero gate voltage drain current	I _{DSS}	_	—	1	μA	V _{DS} = 200 V, V _{GS} = 0
Gate to source leak current	I _{GSS}	_	—	±0.1	μA	V_{GS} = ±30 V, V_{DS} = 0
Gate to source cutoff voltage	V _{GS(off)}	3.0	_	4.5	V	V _{DS} = 10 V, I _D = 1 mA
Forward transfer admittance	y _{fs}	3.5	6.0		S	$I_D = 4.3 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$
Static drain to source on state resistance	R _{DS(on)}	—	0.23	0.27	Ω	I_D = 4.3 A, V_{GS} = 10 V ^{Note4}
Input capacitance	Ciss		430		pF	V _{DS} = 25 V
Output capacitance	Coss		86		pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss		7		pF	
Turn-on delay time	t _{d(on)}		24		ns	I _D = 4.3 A
Rise time	tr	_	24		ns	V_{GS} = 10 V R _L = 23.3 Ω Rg = 10 Ω
Turn-off delay time	t _{d(off)}	_	44		ns	
Fall time	t _f	_	9		ns	
Total gate charge	Qg	_	10		nC	V _{DD} = 160 V
Gate to source charge	Qgs	_	2.7		nC	V _{GS} = 10 V I _D = 8.5 A
Gate to drain charge	Qgd		3.8	_	nC	
Body-drain diode forward voltage	V _{DF}	_	0.9	1.4	V	$I_F = 8.5 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery time	t _{rr}	_	100	_	ns	$I_F = 8.5 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu \text{s}$

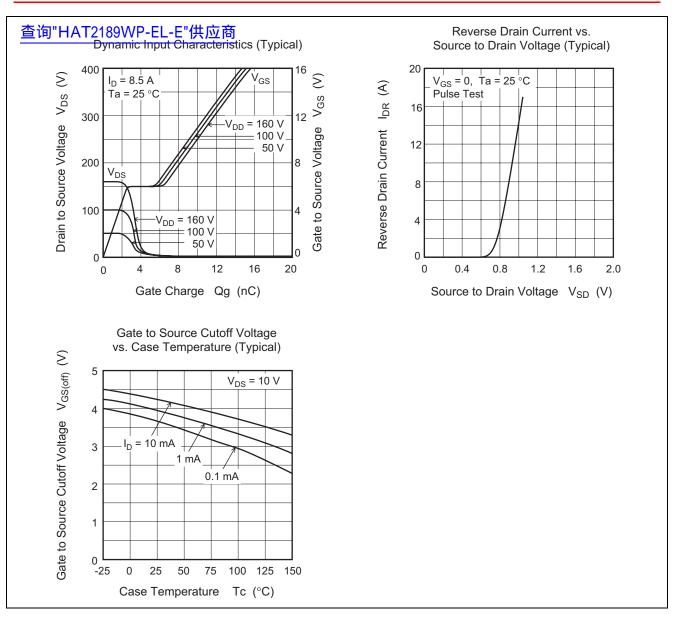
Notes: 4. Pulse test



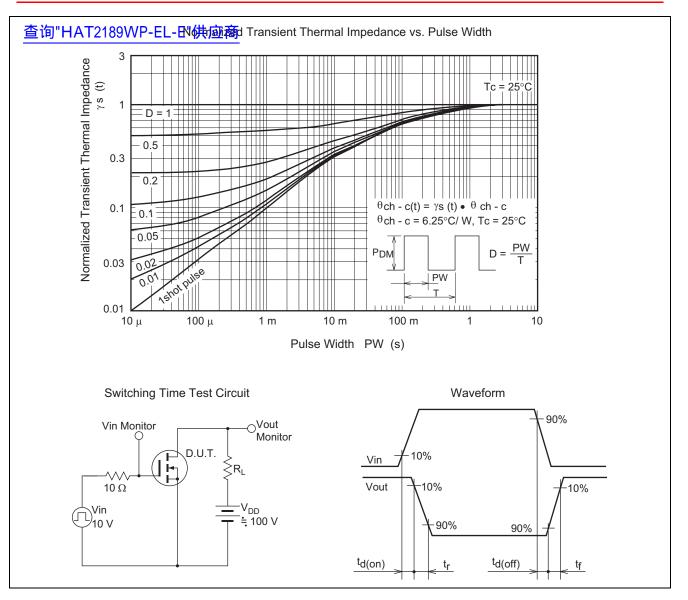
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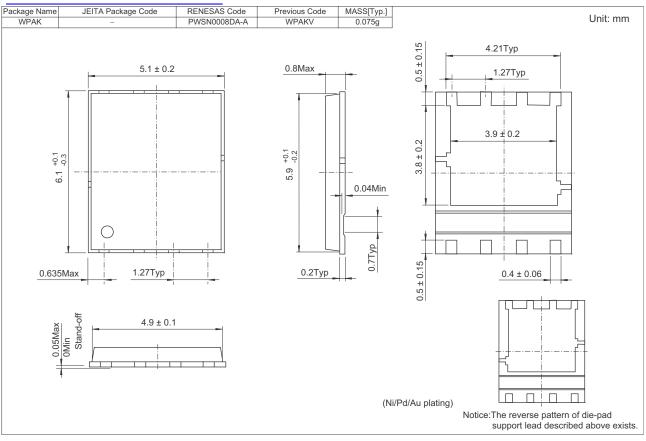








Package Dimensions 它们中的12189WP-EL-E"供应商



Ordering Information

Part No.	Quantity	Shipping Container
HAT2189WP-EL-E	2500 pcs	Taping



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